



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Rds(on) MAX	I _D MAX T _A = +25°C
-30V	$19m\Omega @ VGS = -10V$	-8.7A
-30 V	45mΩ @ VGS = -4.5V	-5.5A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Battery Management Application
- Power Management Functions
- DC-DC Converters

Features and Benefits

- 0.6mm Profile Ideal for Low Profile Applications
- Low Gate Threshold Voltage
- Low On-Resistance
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
 - For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

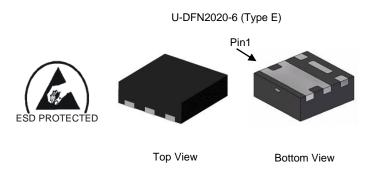
https://www.diodes.com/products/automotive/automotive-products/.

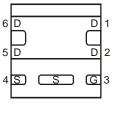
 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

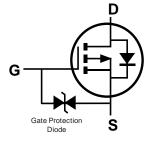
https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.007 grams (Approximate)







Pin Out Bottom View

Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3026SFDE-7	U-DFN2020-6 (Type E)	3,000/Tape & Reel
DMP3026SFDE-13	U-DFN2020-6 (Type E)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

Site 1



7P = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2016		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	D		Н	l	J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



7P = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Year	2016	 2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	6	 0	1	2	3	4	5	6	7	8	9

Week	1-26	27-52	53
Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	X	Υ	Z



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	-30	V		
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drais Current (Note 6) V 40V	Steady State	T _A = +25°C T _A = +70°C	lo	-8.7 -6.9	А
Continuous Drain Current (Note 6) V _{GS} = -10V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	lo	-10.4 -8.4	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	-50	Α
Continuous Source-Drain Diode Current (Note 6)	Is	-2.0	Α		
Avalanche Current (Note 7) L = 0.1mH	las	-23	Α		
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	27	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	D-	0.72	W	
Total Power Dissipation (Note 5)	$T_A = +70^{\circ}C$	PD	0.46	VV	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	ρ	175	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	121	C/VV	
Total Power Dissipation (Note 6)	$T_A = +25$ °C	D-	2.0	W	
Total Fower Dissipation (Note o)	$T_A = +70$ °C	PD	1.3		
Thermal Decistores, Junction to Ambient (Note 6)	Steady State	Б.	61		
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	RθJA	42	°C/W	
Thermal Resistance, Junction to Case (Note 6)	Steady State	R _θ JC	9.3		
Operating and Storage Temperature Range		ТJ, Tsтg	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BVDSS	-30	_	_	V	$Vgs = 0V, ID = -250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C		_	_	-1		\/ 24\/ \/ 0\/
Zero Gate Voltage Drain Current TJ = +150°C (Note 9)	I _{DSS}	-	_	-100	μA	VDS = -24V, $VGS = 0V$
Gate-Source Leakage	Igss	_	_	±10	μΑ	Vgs = ±25V, Vps = 0V
ON CHARACTERISTICS (Note 8)						<u>.</u>
Gate Threshold Voltage	Vgs(TH)	-1	_	-3	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
1			15	19		Vgs = -10V, ID = -4.5A
Static Drain-Source On-Resistance	RDS(ON)	_	28	45	mΩ	Vgs = -4.5V, ID = -3.5A
<u></u> !	<u> </u>		34	54	<u></u>	Vgs = -4.0V, ID = -3.0A
Diode Forward Voltage	VsD	_	-0.7	-1.2	V	Vgs = 0V, Is = -1.0A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	_	1,204	_		451/1/ 01/
Output Capacitance	Coss	_	154	_	pF	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}		112	_		= 1.0 V 2
Gate Resistance	Rg	_	16	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = -10V)	Qg	-	19.6	_		
Total Gate Charge (VGS = -4.5V)	Qg	_	9.2	_	20	45)/ 1 054
Gate-Source Charge	Qgs	-	4.3	_	nC	$V_{DS} = -15V, I_{D} = -9.5A$
Gate-Drain Charge	Qgd	_	3.9	_		
Turn-On Delay Time	t _{D(on)}	_	5.3	_		
Turn-On Rise Time	t _r	_	23	_		$V_{DS} = -15V, V_{GS} = -10V,$
Turn-Off Delay Time	t _{D(off)}	-	34	_	ns	$R_G = 6\Omega$, $I_D = -9.5A$
Turn-Off Fall Time	tf	_	26	_		
Reverse Recovery Time	t _{rr}	_	10	_	ns	
Reverse Recovery Charge	Qrr	_	3.3	_	nC	I _F = -9.5A, di/dt = 100A/μs

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

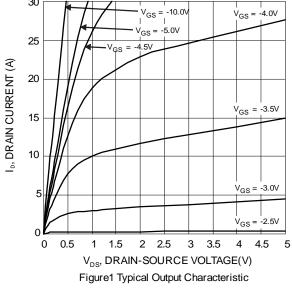
^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

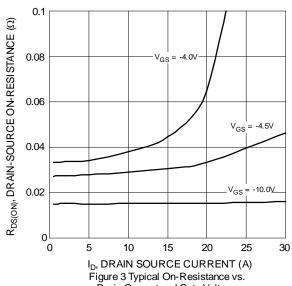
^{7.} I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

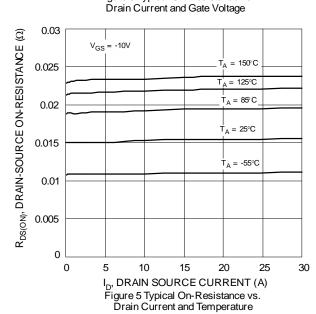
^{8.} Short duration pulse test used to minimize self-heating effect.

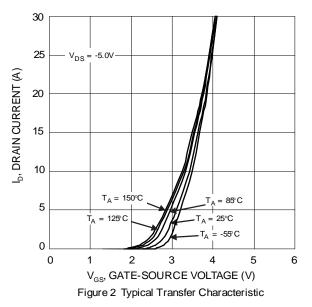
^{9.} Guaranteed by design. Not subject to product testing.

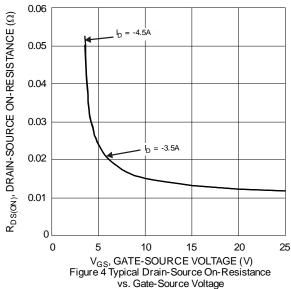












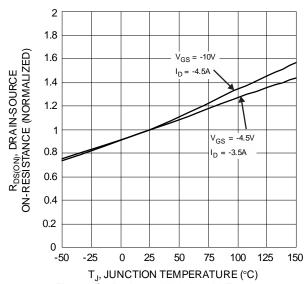
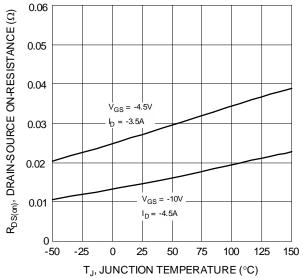
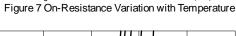
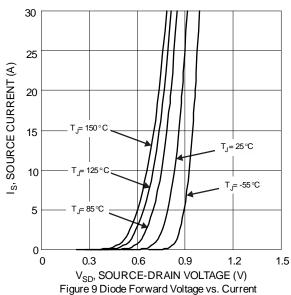


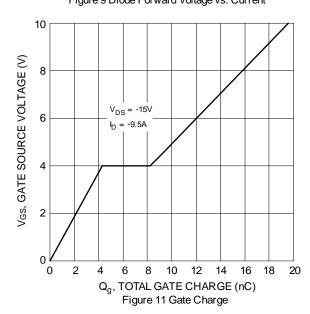
Figure 6 On-Resistance Variation with Temperature











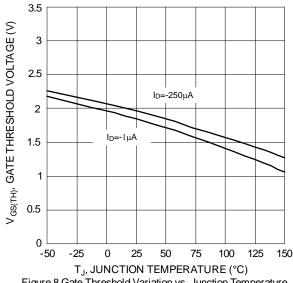
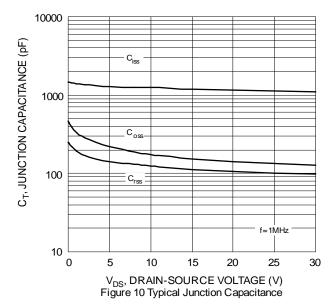
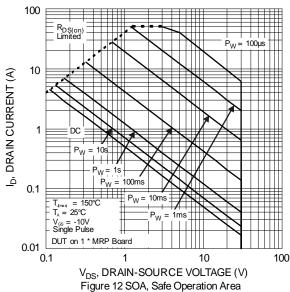


Figure 8 Gate Threshold Variation vs. Junction Temperature







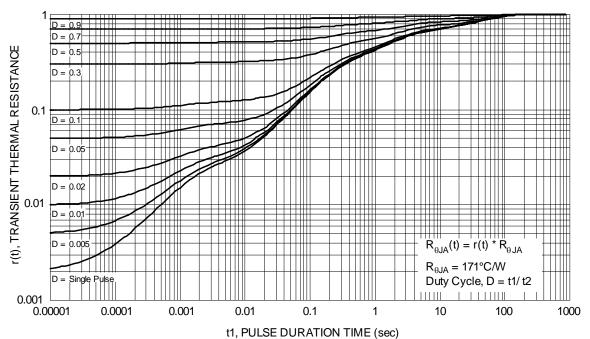


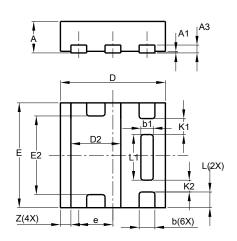
Figure 13 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type E)

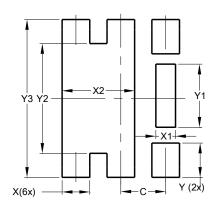


U-DFN2020-6								
Type E								
Dim	Min	Тур						
Α	0.57	0.63	0.60					
A1	0	0.05	0.03					
A3	-	-	0.15					
b	0.25	0.35	0.30					
b1	0.185	0.285	0.235					
D	1.95	2.05	2.00					
D2	0.85	1.05	0.95					
E	1.95	2.05	2.00					
E2	1.40	1.60	1.50					
е		_	0.65					
L	0.25	0.35	0.30					
L1	0.82	0.92	0.87					
K1	-	_	0.305					
K2	_	_	0.225					
Z	-	-	0.20					
All	Dimen	sions i	in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type E)



Dimensions	value (in mm)
С	0.650
Х	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300



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